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APPLICATION NO.	FILI	NG DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/660,779	09/	/12/2003	Mun-Pyo Hong	6192.0159.D2	5768	
7590 03/14/2005				EXAMINER		
McGuireWood	ds LLP		WEISS, HOWARD			
Suite 1800 1750 Tysons Bo	oulevard		ART UNIT	PAPER NUMBER		
McLean, VA 22102				2814		
·				DATE MAILED: 03/14/2005		

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)	
	10/660,779	HONG ET AL.	
Office Action Summary	Examiner	Art Unit	
	Howard Weiss	2814	·
The MAILING DATE of this communication ap Period for Reply	pears on the cover sheet with	the correspondence address	S
A SHORTENED STATUTORY PERIOD FOR REPL THE MAILING DATE OF THIS COMMUNICATION: - Extensions of time may be available under the provisions of 37 CFR 1. after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply 16 NO period for reply is specified above, the maximum statutory period and 17 Failure to reply within the set or extended period for reply will, by status any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	136(a). In no event, however, may a rep ply within the statutory minimum of thirty (d will apply and will expire SIX (6) MONTH te, cause the application to become ABAN	ly be timely filed 30) days will be considered timely. IS from the mailing date of this commun IDONED (35 U.S.C. § 133).	nication.
Status			
 1) ⊠ Responsive to communication(s) filed on 28 I 2a) ⊠ This action is FINAL. 2b) ☐ This 3) ☐ Since this application is in condition for allowed closed in accordance with the practice under 	is action is non-final. ance except for formal matter		rits is
Disposition of Claims			
4) ☐ Claim(s) 28-30 is/are pending in the application 4a) Of the above claim(s) is/are withdress. 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 28-30 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and/	awn from consideration.		
Application Papers			
9) The specification is objected to by the Examination 10) The drawing(s) filed on <u>28 December 2004</u> is Applicant may not request that any objection to the Replacement drawing sheet(s) including the correction of the oath or declaration is objected to by the Examination is objected to by the Examination is objected.	/are: a)⊠ accepted or b)□ of edition described accepted or b)□ of the drawing(s) be held in abeyance of the drawing(s	e. See 37 CFR 1.85(a).) is objected to. See 37 CFR 1.	121(d).
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority application from the International Burest * See the attached detailed Office action for a list	nts have been received. Ints have been received in Appoint to documents have been real (PCT Rule 17.2(a)).	plication No eceived in this National Stag	je
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08 Paper No(s)/Mail Date	Paper No(s)/	mmary (PTO-413) Mail Date ormal Patent Application (PTO-152))

Attorney's Docket Number: 6192.0159.D2

Filing Date: 9/12/03

Continuing Data: Division of 09/676,813 (10/2/00 now U.S. Patent No. 6,674,495)

Claimed Foreign Priority Date: 9/30/00, 12/27/99, 9/4/00 (KRX)

Applicant(s): Hong et al. (Hong, Kim, Rho, Kang, Kim)

Examiner: Howard Weiss

Drawings

1. The drawings were received on 12/28/04. These drawings are acceptable.

Claim Rejections - 35 USC § 103

- 2. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

3. Claims 28 and 29 are rejected under 35 U.S.C. 103(a) as being unpatentable over Mishima et al. (JP 02-179977), Kaneko (JP 06-77483) and Huang et al. (U.S. Patent No. 5,354,700).

Mishima et al. show most aspects of the instant invention (e.g. Figures 1, 3, 4 and 7) including:

- > a plurality of pixels defined by gate and data lines
- > a plurality of thin film transistors and pixel electrodes
- > said transistors each having an amorphous silicon (aSi) semiconductor layer 24 and an ohmic layer 26

Mishima et al. do not show the semiconductor layer comprising a double-layered structure with an upper aSi layer with a lower band gap than a lower aSi layer. Kaneko teaches (e.g. Figure 1) to use a semiconductor layer 3 comprising a double-layered structure with upper 3b and lower 3a aSi layers to form a thin-film transistor whose throughput is not spoiled and is of good characteristics (see Constitution). It would have been obvious to a person of ordinary skill in the art at the time of invention to use a semiconductor layer comprising a double-layered structure with upper and lower aSi layers as taught by Kaneko in the device of Mishima et al. to form a thin-film transistor whose throughput is not spoiled and is of good characteristics.

Huang et al. teaches (e.g. Figure 2) to form a semiconductor layer with the upper layer 36 having a lower band gap then the lower layer 35 to provide a transistor with high mobility, high transconductance and excellent hot carrier immunity (Column 1 Lines 24 to 27). It would have been obvious to a person of ordinary skill in the art at the time of invention to form a semiconductor layer with the upper layer having a lower band gap then the lower layer as taught by Huang et al. in the device of Mishima et al. to provide a transistor with high mobility, high transconductance and excellent hot carrier immunity.

4. Claim 30 is rejected under 35 U.S.C. 103(a) as being unpatentable over Nakanishi et al. (U.S. Patent No. 6,548,828), Rho et al. (U.S. Patent No. 6,057,8963) and Kobayashi (U.S. Patent No. 5,202,572).

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Nakanishi et al. show most aspects of the instant invention (e.g. Figures 1 and 2 and Column 1 Lines 63 to 67) including:

- a plurality of pixels defined by gate and data lines
- > a plurality of thin film transistors and pixel electrodes
- > said thin film transistors having a gate insulating layer includes lower 23 and upper 24 layers

Nakanishi et al. do not show the use of amorphous silicon nitride or organic material as gate insulating material. Kobayashi teaches (e.g. Figure 6(G) and Column 5 Lines 54 to 58) to use amorphous silicon nitride for gate material 30 to provide a thin film transistor with smaller variation of the on/off currents (Column 3 Lines 6 to 10). It would have been obvious to a person of ordinary skill in the art at the time of invention to use amorphous silicon nitride for gate material as taught by Kobayashi in the device of Nakanishi et al. to provide a thin film transistor with smaller variation of the on/off currents.

Rho et al. teach (e.g. Column 2 Lines 54 to 57) to use organic material as gate insulating material to reduce the parasitic capacitance between the gate and drain electrodes. It would have been obvious to a person of ordinary skill in the art at the time of invention to use organic material as gate insulating material as taught by Rho et al. in the device of Nakanishi et al. to reduce the parasitic capacitance between the gate and drain electrodes.

Response to Arguments

5. Applicant's arguments with respect to Claims 28 to 30 have been considered but are most in view of the new ground(s) of rejection.

Conclusion

6. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP

§ 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

- 7. Paper copies of cited U.S. patents and U.S. patent application publications will cease to be mailed to applicants with Office actions as of June 2004. Paper copies of foreign patents and non-patent literature will continue to be included with office actions. These cited U.S. patents and patent application publications are available for download via the Office's PAIR. As an alternate source, all U.S. patents and publications are available on the USPTO web site patent application (www.uspto.gov), from the Office of Public Records and from commercial sources Business referred to the Electronic Center (EBC) Applicants are http://www.uspto.gov/ebc/index.html or 1-866-217-9197 for information on this policy. Requests to restart a period for response due to a missing U.S. patent or patent application publications will not be granted.
- 8. Papers related to this application may be submitted directly to Art Unit 2814 by facsimile transmission. The faxing of such papers must conform with the notice published in the Official Gazette, 1096 OG 30 (15 November 1989). The Art Unit 2814 Fax Center number is (703) 872-9306. The Art Unit 2814 Fax Center is to be used only for papers related to Art Unit 2814 applications.

9. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Howard Weiss at (571) 272-1720 and between the hours of 8:00 AM to 4:00 PM (Eastern Standard Time) Monday through Friday or by e-mail via Howard.Weiss@uspto.gov.

10. The following list is the Examiner's field of search for the present Office Action:

Field of Search	Date
U.S. Class / Subclass(es): 25759, 63; 349/43	thru 3/9/05
Other Documentation: none	
Electronic Database(s): EAST	thru 3/9/05

HW/hw 9 March 2005 Howard Weiss Primary Examiner Art Unit 2814